

NVMFS5A160PLZ

MOSFET – Power, Single P-Channel

-60 V, -100 A, 7.7 mΩ



ON Semiconductor®

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Features

- Small Footprint (5 x 6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- NVMFS5A160PLZWF: Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

V_{DSS}	$R_{DS(on)}$ MAX	I_D MAX
-60 V	7.7 mΩ @ -10 V	-100 A
	10.5 mΩ @ -4.5 V	

SPECIFICATION MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (Notes 1, 2, 3)

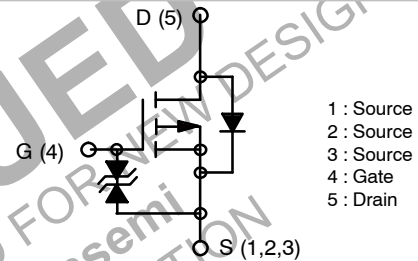
Symbol	Parameter	Value	Unit
V_{DSS}	Drain to Source Voltage	-60	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Continuous Drain, Current $R_{\theta JC}$, (Notes 1, 3)	Steady State	$T_C = 25^\circ\text{C}$
		$T_C = 25^\circ\text{C}$	-100
P_D	Power Dissipation $R_{\theta JC}$ (Note 1)	200	W
I_D	Continuous Drain: Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$
		$T_A = 25^\circ\text{C}$	-15
P_D	Power Dissipation $R_{\theta JA}$ (Note 1, 2)	3.8	W
I_{DP}	Pulsed Drain Current	$PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$	-400
T_J, T_{STG}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$
I_S	Source Current (Body Diode)	-100	A
E_{AS}	Single Pulse Drain to Source Avalanche Energy ($L = 1.0 \text{ mH}$, $I_{L(pk)} = -26 \text{ A}$)	335	mJ
T_L	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

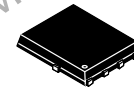
THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Junction to Case Steady State	0.75	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction to Ambient Steady State (Note 3)	39	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

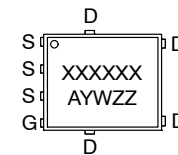


P-CHANNEL MOSFET



DFN5 (SO-8FL)

MARKING DIAGRAM



- XXXXXX = Specific Device Code
5A160L(NVMFS5A160PLZ)
160LWF(NVMFS5A160PLZWF)
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NVMFS5A160PLZ

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain to Source Breakdown Voltage	$I_D = -1\text{ mA}, V_{GS} = 0\text{ V}$	-60			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$		-1.0	μA
			$T_J = 100^\circ\text{C}$ (Note 4)		-100	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$			± 10	μA

ON CHARACTERISTICS (Note 5)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$	-1.2		-2.6	V
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = -10\text{ V}$	$I_D = -50\text{ A}$	5.8	7.7	$m\Omega$
		$V_{GS} = -4.5\text{ V}$	$I_D = -50\text{ A}$	7.3	10.5	
g_{FS}	Forward Transconductance	$V_{DS} = -10\text{ V}, I_D = -50\text{ A}$		119		S

CHARGES, CAPACITANCES & GATE RESISTANCE

C_{iss}	Input Capacitance	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ $V_{DS} = -20\text{ V},$		7700		pF
C_{oss}	Output Capacitance			720		
C_{rss}	Reverse Transfer Capacitance			540		
$Q_{g(tot)}$	Total Gate Charge	$V_{GS} = -10\text{ V}, I_D = -50\text{ A}$ $V_{DS} = -36\text{ V},$		160		nC
Q_{gs}	Gate to Source Charge			24		
Q_{gd}	Gate to Drain Charge			45		

SWITCHING CHARACTERISTICS (Note 6)

$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = -36\text{ V}, I_D = -50\text{ A},$ $V_{GS} = -10\text{ V},$ $R_G = 50\ \Omega$		50		ns
t_r	Rise Time			690		
$t_{d(off)}$	Turn-Off Delay Time			645		
t_f	Fall Time			643		

DRAIN-SOURCE DIODE CHARACTERISTICS

V_{SD}	Forward Diode Voltage	$V_{GS} = 0\text{ V}, I_S = -50\text{ A}$		-0.83	-1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = -50\text{ A}$		93		ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 100\text{ A}/\mu\text{s}$		218		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at $T_J = 100^\circ\text{C}$. Product is not tested to this condition in production.
5. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

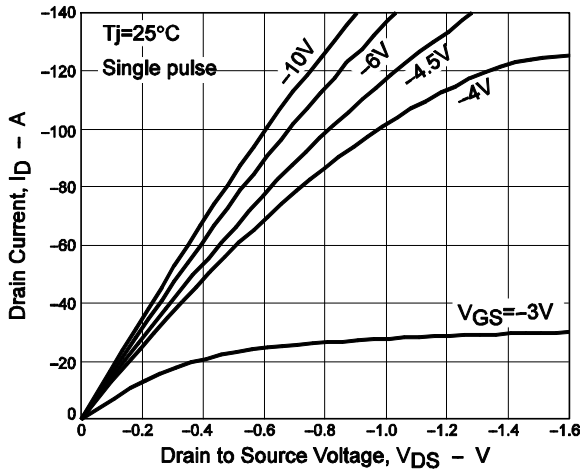


Figure 1. $I_D - V_{DS}$

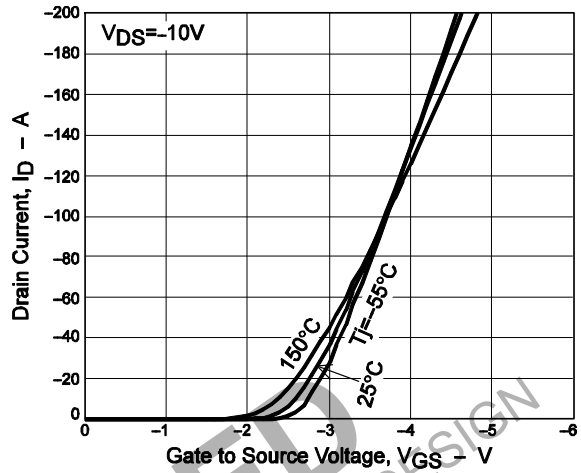


Figure 2. $I_D - V_{GS}$

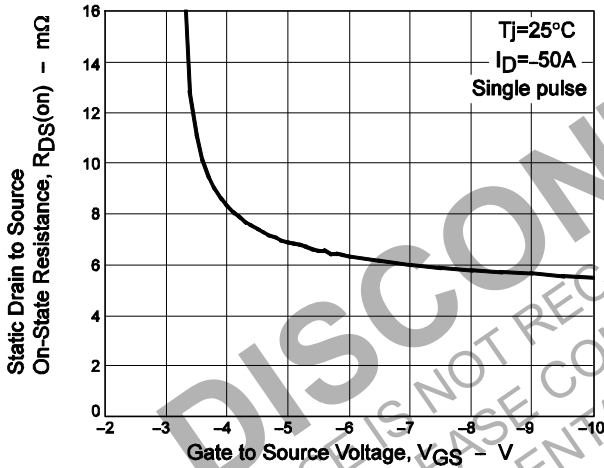


Figure 3. $R_{DS(on)} - V_{GS}$

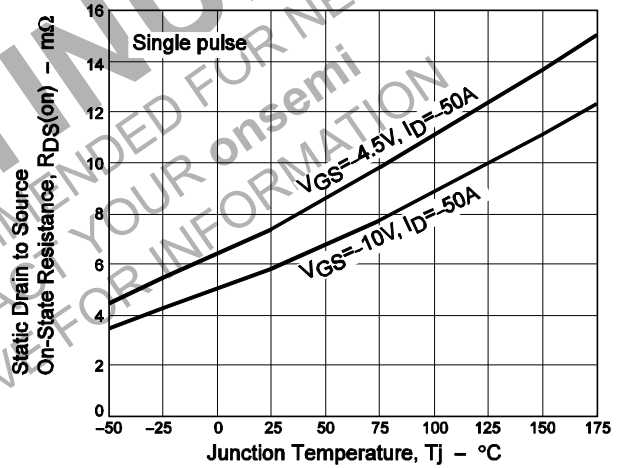


Figure 4. $R_{DS(on)} - T_J$

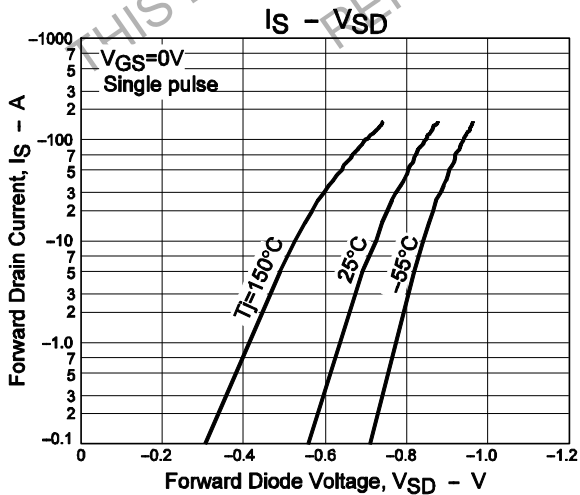


Figure 5. $I_S - V_{SD}$

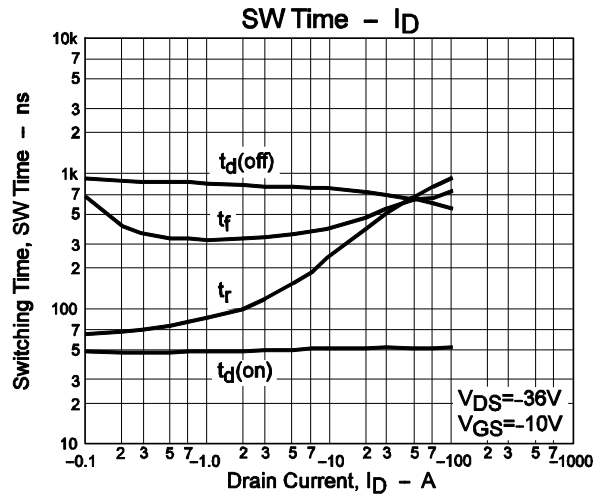


Figure 6. SW Time - I_D

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TYPICAL CHARACTERISTICS

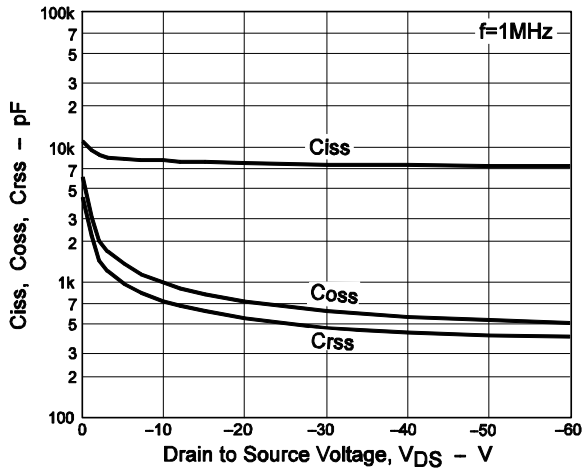


Figure 7. C_{iss} , C_{oss} , C_{rss} - V_{DS}

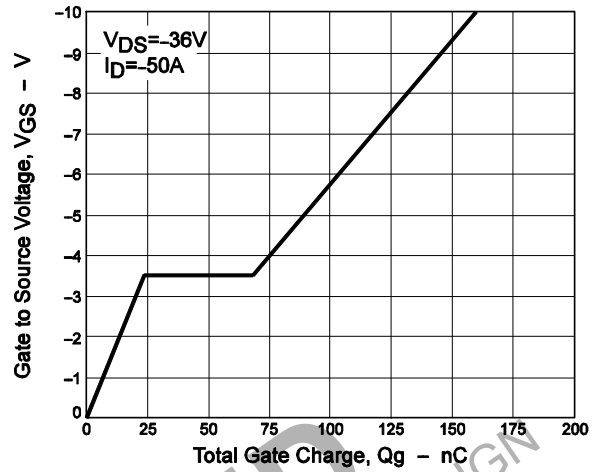


Figure 8. V_{GS} - Q_g

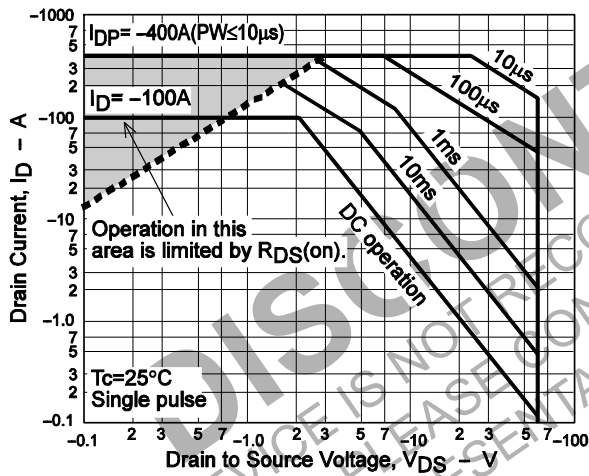


Figure 9. SOA

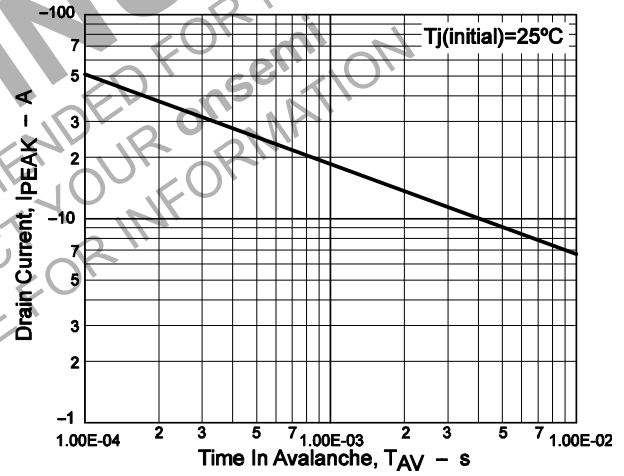


Figure 10. I_{PEAK} - T_{AV}

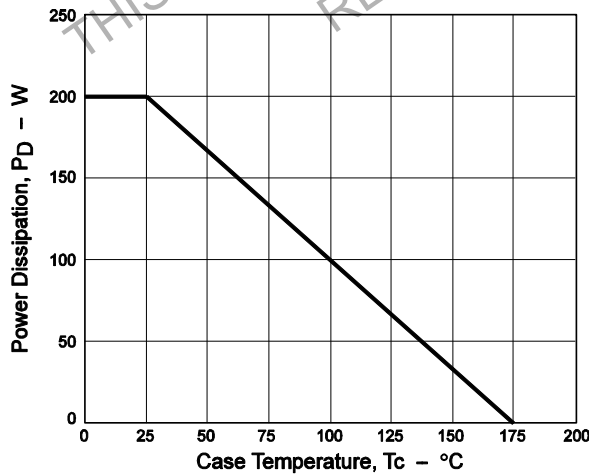


Figure 11. P_D - T_C

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TYPICAL CHARACTERISTICS

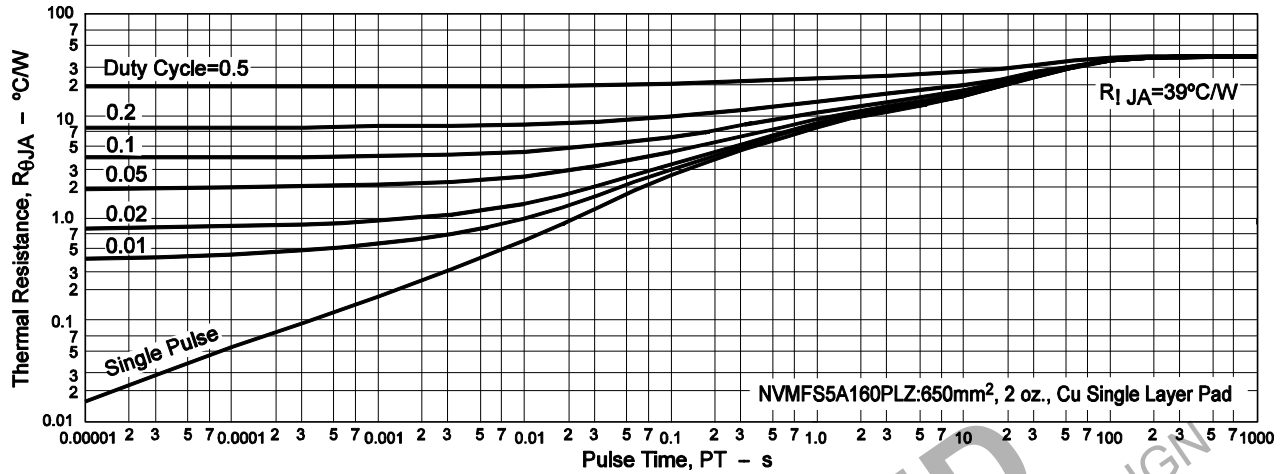


Figure 12. $R_{\theta JA}$ - Pulse Time

ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing) [†]
NVMFS5A160PLZT1G	5A160L	DFN5 5x6, 1.27P (SO-8FL) (Pb-Free)	1.500 / Tape & Reel
NVMFS5A160PLZWFT1G	160LWF	DFN5 5x6, 1.27P (SO-8FL) (Pb-Free, Wettable Flanks)	1.500 / Tape & Reel
NVMFS5A160PLZT3G	5A160L	DFN5 5x6, 1.27P (SO-8FL) (Pb-Free)	5.000 / Tape & Reel
NVMFS5A160PLZWFT3G	160LWF	DFN5 5x6, 1.27P (SO-8FL) (Pb-Free, Wettable Flanks)	5.000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



1
SCALE 2:1

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



- STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
- STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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